

Fast Switching Diode



Features

- 600V diode technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Qualified according to JEDEC for target applications

Product Summary

V_{RRM}	600	V
I_F	30	A
V_F	1.5	V
T_{jmax}	175	°C



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDP30E60	PG-TO220-2	-	D30E60	C	A	-

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current $T_C = 25\text{ °C}$ $T_C = 90\text{ °C}$	I_F	52.3 34.9	A
Surge non repetitive forward current $T_C = 25\text{ °C}$, $t_p = 10\text{ ms}$, sine halfwave	I_{FSM}	117	A
Maximum repetitive forward current $T_C = 25\text{ °C}$, t_p limited by $t_{j,max}$, $D = 0.5$	I_{FRM}	81	A
Power dissipation $T_C = 25\text{ °C}$ $T_C = 90\text{ °C}$	P_{tot}	142.9 80.9	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature 1.6mm (0.063 in.) from case for 10 s	T_S	260	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1.05	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ¹⁾		-	35	-	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Reverse leakage current $V_R=600V, T_j=25^{\circ}C$ $V_R=600V, T_j=150^{\circ}C$	I_R	- -	- -	50 2500	μA
Forward voltage drop $I_F=30A, T_j=25^{\circ}C$ $I_F=30A, T_j=150^{\circ}C$	V_F	- -	1.5 1.5	2 -	V

⁰J-STD20 and JESD22

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

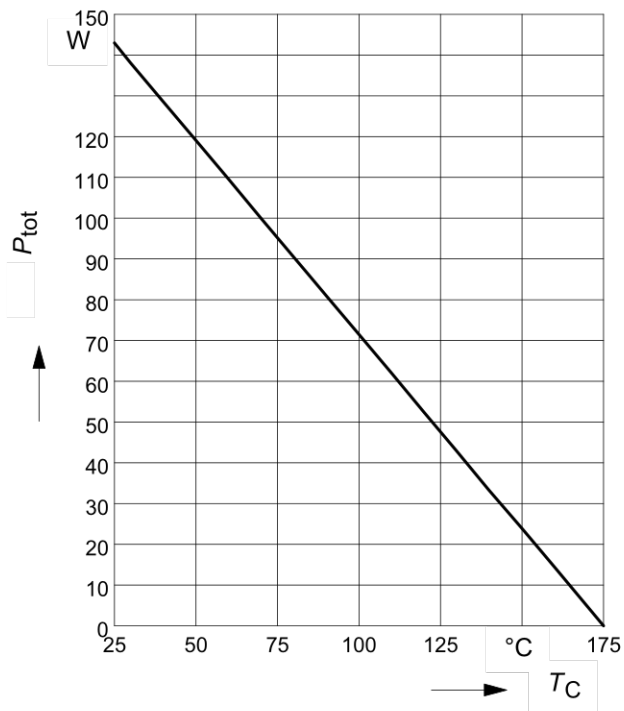
Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=25^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=125^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=150^{\circ}C$	t_{rr}	- - -	126 171 178	- - -	ns
Peak reverse current $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=25^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=125^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=150^{\circ}C$	I_{rrm}	- - -	19 22 24	- - -	A
Reverse recovery charge $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=25^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=125^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=150^{\circ}C$	Q_{rr}	- - -	1100 1950 2150	- - -	nC
Reverse recovery softness factor $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=25^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=125^{\circ}C$ $V_R=400V$, $I_F=30A$, $di_F/dt=1000A/\mu s$, $T_j=150^{\circ}C$	S	- - -	4 4.6 4.8	- - -	

1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

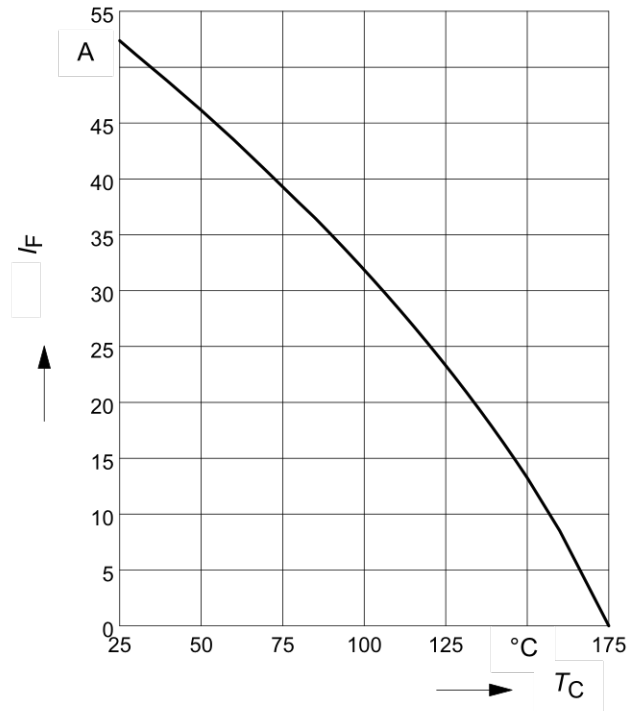
parameter: $T_j \leq 175^\circ\text{C}$



2 Diode forward current

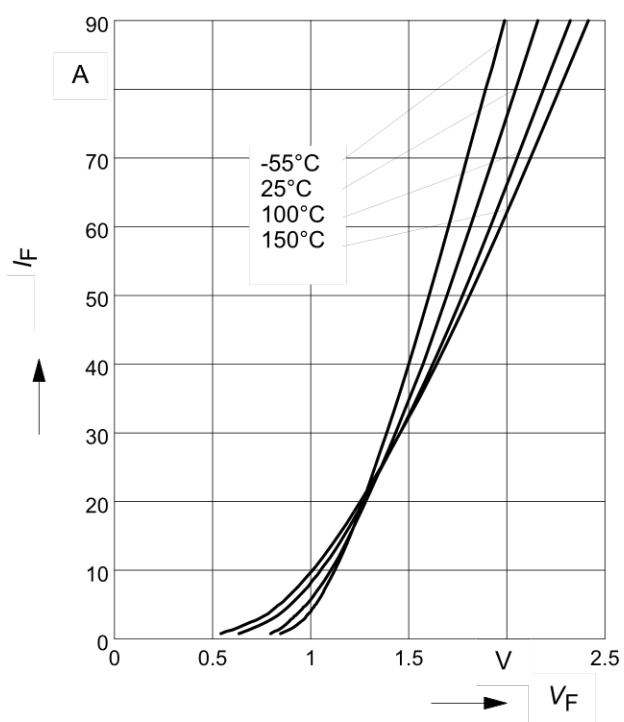
$$I_F = f(T_C)$$

parameter: $T_j \leq 175^\circ\text{C}$



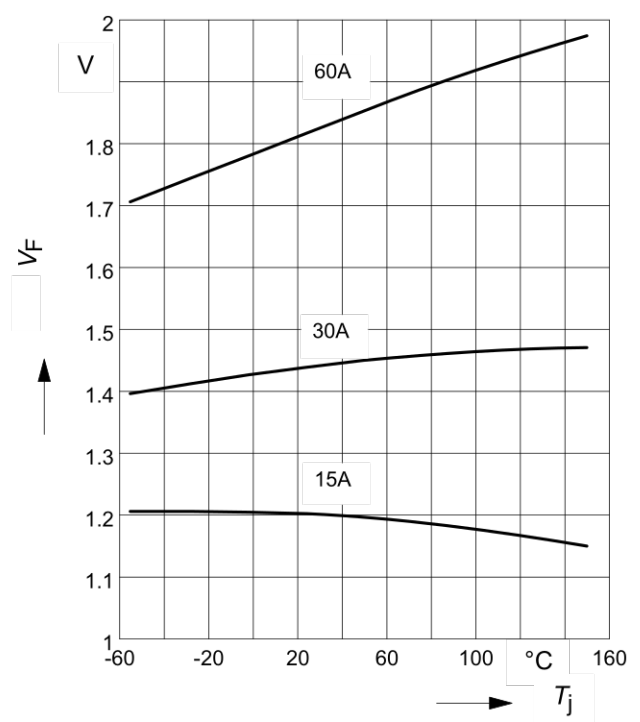
3 Typ. diode forward current

$$I_F = f(V_F)$$



4 Typ. diode forward voltage

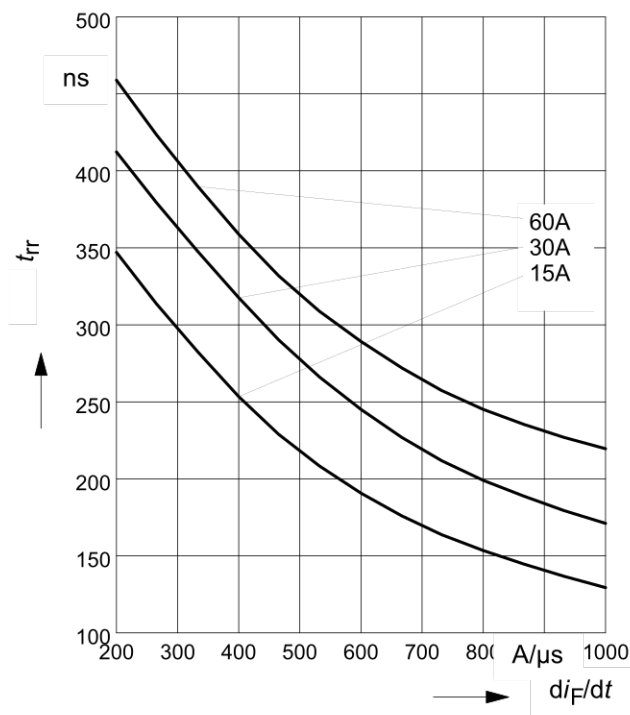
$$V_F = f(T_j)$$



5 Typ. reverse recovery time

$$t_{rr} = f(dI_F/dt)$$

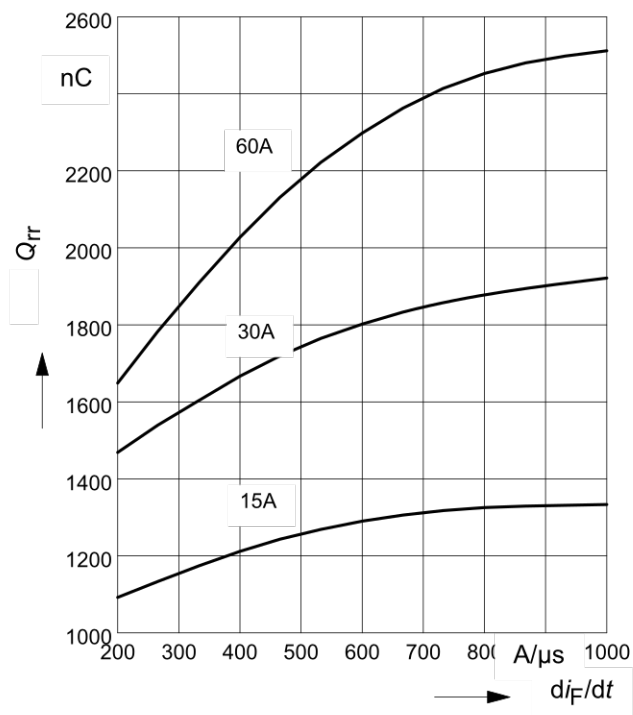
parameter: $V_R = 400V$, $T_j = 125^\circ C$



6 Typ. reverse recovery charge

$$Q_{rr} = f(dI_F/dt)$$

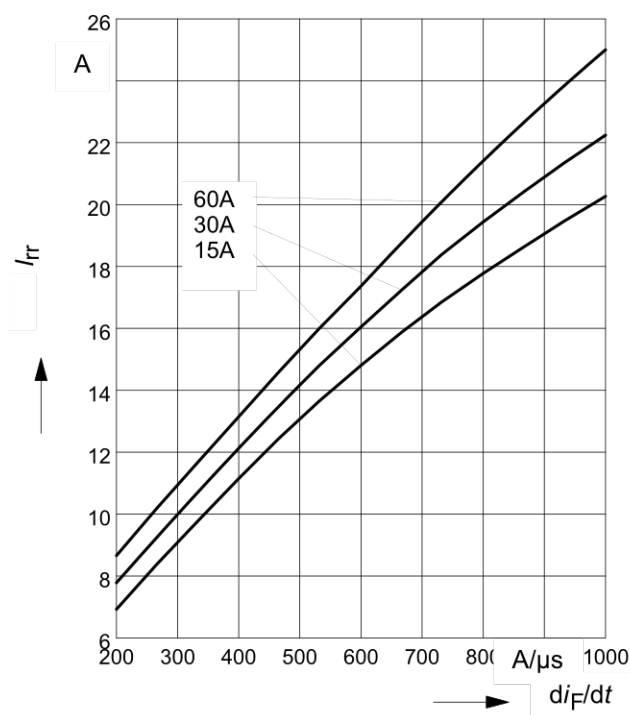
parameter: $V_R = 400V$, $T_j = 125^\circ C$



7 Typ. reverse recovery current

$$I_{rr} = f(dI_F/dt)$$

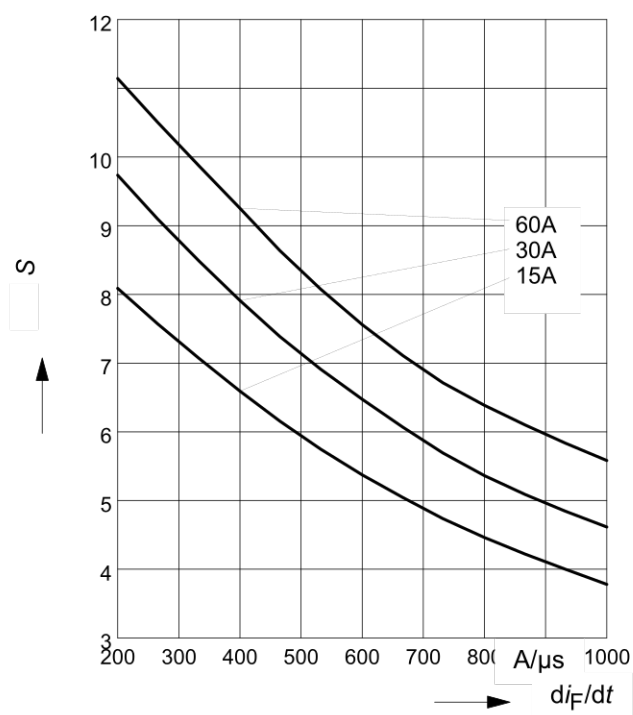
parameter: $V_R = 400V$, $T_j = 125^\circ C$



8 Typ. reverse recovery softness factor

$$S = f(dI_F/dt)$$

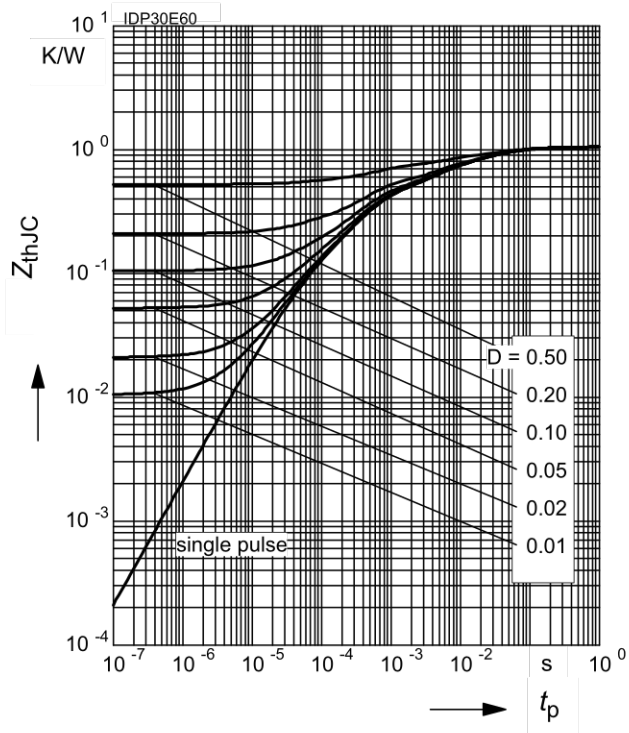
parameter: $V_R = 400V$, $T_j = 125^\circ C$



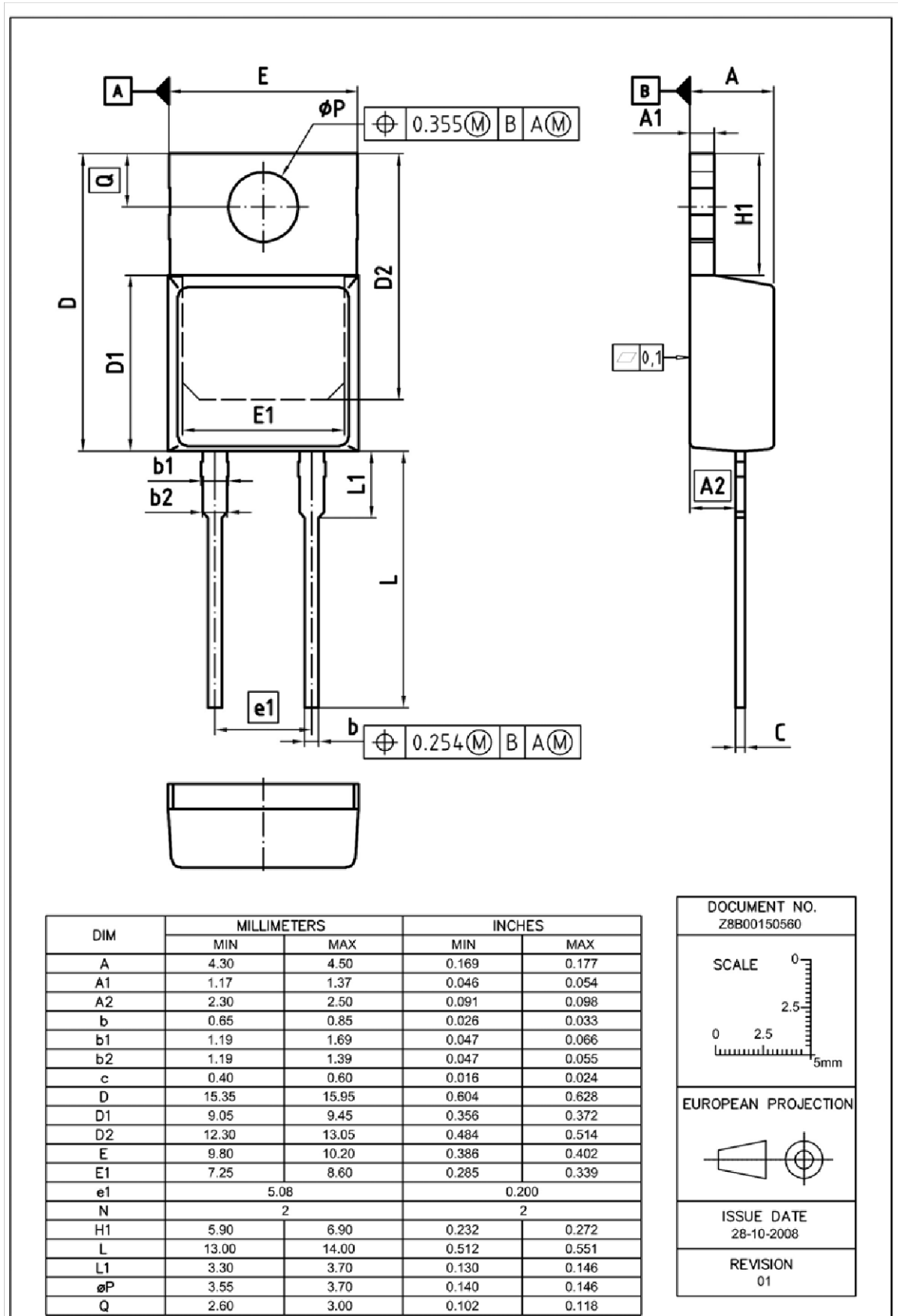
9 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$



Package Outline: TO220-2





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